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Harry J. Levinson
Mircea V. Dusa
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Bruce W. Smith, Rochester Institute of Technology (USA)
Akiyoshi Suzuki, Canon, Inc. (Japan)
Geert Vandenberghe, IMEC (Belgium)

Session Chairs

- 1 Keynote Session
Harry J. Levinson, Advanced Micro Devices, Inc. (USA)
Mircea V. Dusa, ASML US, Inc. (USA)
- 2 Double Masking I
Geert Vandenberghe, IMEC (Belgium)
Willard E. Conley, Freescale Semiconductor, Inc. (USA)
- 3 Double Masking II
Tomoyuki Matsuyama, Nikon Corporation (Japan)
Geert Vandenberghe, IMEC (Belgium)

- 4 Low-k1 Lithography I
Tatsuhiko Higashiki, Toshiba Corporation (Japan)
Kafai Lai, IBM Microelectronics Division (USA)
- 5 Low-k1 Lithography II
Wilhelm Maurer, Infineon Technologies AG (Germany)
Ken Ozawa, Sony Atsugi Technology Center (Japan)
- 6 Double Masking III
Sam Sivakumar, Intel Corporation (USA)
Pary Baluswamy, Micron Technology, Inc. (USA)
- 7 Simulation I
Kafai Lai, IBM Microelectronics Division (USA)
Nigel R. Farrar, Cymer, Inc. (USA)
- 8 Simulation II
Akiyoshi Suzuki, Canon, Inc. (Japan)
Tatsuhiko Higashiki, Toshiba Corporation (Japan)
- 9 High Index Immersion Lithography
Willard E. Conley, Freescale Semiconductor, Inc. (USA)
Sam Sivakumar, Intel Corporation (USA)
- 10 Process I
Nigel R. Farrar, Cymer, Inc. (USA)
Wilhelm Maurer, Infineon Technologies AG (Germany)
- 11 OPC and Mask Technology
Willard E. Conley, Freescale Semiconductor, Inc. (USA)
Bruce W. Smith, Rochester Institute of Technology (USA)
- 12 Process II
Roger H. French, DuPont Company (USA)
Pary Baluswamy, Micron Technology, Inc. (USA)
- 13 Lithography Tools I
Willard E. Conley, Freescale Semiconductor, Inc. (USA)
Tatsuhiko Higashiki, Toshiba Corporation (Japan)
- 14 Lithography Tools II
Ken Ozawa, Sony Atsugi Technology Center (Japan)
Roger H. French, DuPont Company (USA)